

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions,  
and listings, of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A nonvolatile semiconductor memory device, comprising:

a semiconductor substrate having thereon a plurality of diffusion layers for forming bit lines and a plurality of channel regions disposed between said adjacent diffusion layers;

an insulating film formed on said semiconductor substrate for trapping electric charge;

an electrical conductive film formed on said insulating film for forming a word line; and

an oxide film formed on said insulating film on said diffusion layers,

wherein said insulating film is generally flatly formed on both said diffusion layers and said channel regions, and

wherein said electrical conductive film comprises at least a first electrical conductive film formed on said insulating film on said channel regions and a second electrical conductive film covering said first electrical conductive film,

said oxide film being formed by oxidizing said first electrical conductive film.

2-3. (canceled)

4. (currently amended) A nonvolatile semiconductor memory device, comprising:

a semiconductor substrate having thereon a plurality of diffusion layers for forming bit lines and a plurality of channel regions disposed between said adjacent diffusion layers;

an oxide film on said diffusion layers;

an insulating film formed on said semiconductor substrate for trapping electric charge; and

an electrical conductive film formed on said insulating film for forming a word line,

wherein said insulating film is generally flatly formed on said channel region, and

wherein said electrical conductive film comprises at least a first electrical conductive film formed on said insulating film on said channel region and a second electrical conductive film covering said first electrical conductive film, said oxide film being formed by oxidizing said first electrical conductive film and said insulating film.

5. (canceled)

6. (original) The nonvolatile semiconductor memory device according to claim 4, wherein said insulating film is formed such that the thickness of said insulating film is smaller on said diffusion layers than the thickness thereof on said channel regions.

7. (currently amended) The nonvolatile semiconductor memory device according to claim [[2]] 1, wherein said first electrical conductive film includes polycrystalline silicon, amorphous silicon, or a silicon compound, and wherein said second electrical conductive film includes polysilicon or refractory metal silicide.

8. (original) The nonvolatile semiconductor memory device according to claim 4, wherein said first electrical conductive film includes polycrystalline silicon, amorphous silicon, or a silicon compound, and wherein said second electrical conductive film includes polysilicon or refractory metal silicide.

9. (original) The nonvolatile semiconductor memory device according to claim 1, wherein said insulating film comprises ON films, said ON films being formed by depositing a silicon oxide film and subsequently depositing a silicon nitride

film thereon, or ONO films, said ONO films being formed by depositing a silicon oxide film, subsequently depositing a silicon nitride film thereon and subsequently depositing a silicon oxide film thereon.

10. (original) The nonvolatile semiconductor memory device according to claim 4, wherein said insulating film comprises ON films, said ON films being formed by depositing a silicon oxide film and subsequently depositing a silicon nitride film thereon, or ONO films, said ONO films being formed by depositing a silicon oxide film, subsequently depositing a silicon nitride film thereon and subsequently depositing a silicon oxide film thereon.

11. (original) The nonvolatile semiconductor memory device according to claim 9, wherein parts of said silicon nitride film of said ON films or said ONO films formed on said diffusion layers are transmuted by ion-implantation.

12. (original) The nonvolatile semiconductor memory device according to claim 10, wherein parts of said silicon nitride film of said ON films or said ONO films formed on said diffusion layers are transmuted by ion-implantation.

13-25. (canceled)